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SLLS725A-JUNE 2006-REVISED JULY 2006

FEATURES

- ESD Protection for RS-232 Bus Pins
 - ±15-kV Human-Body Model (HBM)
 - ±8-kV IEC 61000-4-2, Contact Discharge
 - ±15-kV IEC 61000-4-2, Air-Gap Discharge
- Meet or Exceed the Requirements of TIA/EIA-232-F and ITU v.28 Standards
- Operate With 3-V to 5.5-V V_{CC} Supply
- · Operate up to 1000 kbit/s
- Two Drivers and Two Receivers
- Low Standby Current . . . 1 μA Typ
- External Capacitors . . . 4 × 0.1 μF
- Accepts 5-V Logic Input With 3.3-V Supply

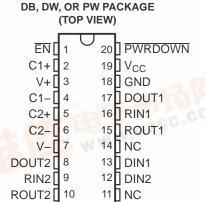
APPLICATIONS

- Battery-Powered Systems
- PDAs
- Notebooks
- Laptops
- Palmtop PCs
- Hand-Held Equipment

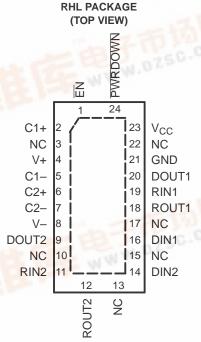
DESCRIPTION/ ORDERING INFORMATION

The SN65C3222E and SN75C3222E consist of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND).

The devices meet the requirements of TIA/EIA-232-F and provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at typical data signaling rates up to 1000 kbit/s and are improved drop-in replacements for industry-popular '3222 two-driver, two-receiver functions.



NC - No internal connection



NC - No internal connection

The SN65C3222E and SN75C3222E can be placed in the power-down mode by setting the power-down ($\overline{PWRDOWN}$) input low, which draws only 1 μA from the power supply. When the devices are powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled; V+ is lowered to V_{CC} , and V_{CC} is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting enable (\overline{EN}) high.



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Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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ORDERING INFORMATION

T _A	PA	CKAGE ⁽¹⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	SOIC - DW	Tube of 25	SN75C3222EDW	75C3222E
	301C - DVV	Reel of 2000	SN75C3222EDWR	7503222E
0°C to 70°C	SSOP – DB	Tube of 70	SN75C3222EDB	MY222E
0.0 10 70.0	220b – DB	Reel of 2000	SN75C3222EDBR	IVITZZZE
	TSSOP – PW	Tube of 70	SN75C3222EPW	- MY222E
	1330F – FW	Reel of 2000	SN75C3222EPWR	IVIT ZZZE
	SOIC - DW	Tube of 25	SN65C3222EDW	- 65C3222E
	30IC - DVV	Reel of 2000	SN65C3222EDWR	00C3222E
–40°C to 85°C	SSOP – DB	Tube of 70	SN65C3222EDB	MU222E
-40 C to 65 C	330F - DB	Reel of 2000	SN65C3222EDBR	IVIUZZZE
	TSSOP – PW	Tube of 70	SN65C3222EPW	MU222E
	1330F - PW	Reel of 2000	SN65C3222EPWR	IVIUZZZL

⁽¹⁾ Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLES

Each Driver(1)

IN	PUTS	OUTPUT
DIN	PWRDOWN	DOUT
X	L	Z
L	Н	Н
Н	Н	L

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

Each Receiver⁽¹⁾

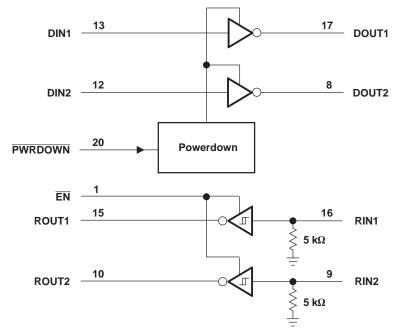
INPU	JTS	OUTPUT
RIN	EN	ROUT
L	L	Н
Н	L	L
X	Н	Z
Open	L	Н

⁽¹⁾ H = high level, L = low level, X = irrelevant,

Open = input disconnected or connected driver off

Z = high impedance (off),

LOGIC DIAGRAM (POSITIVE LOGIC)



Pin numbers are for the DB, DW, and PW packages.

Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V _{CC}	Supply voltage range ⁽²⁾	-0.3	6	V	
V+	Positive-output supply voltage range ⁽²⁾		-0.3	7	V
V-	Negative-output supply voltage range (2)		0.3	-7	V
V+ - V-	Supply voltage difference (2)			13	V
.,	land to the second	Driver (EN, PWRDOWN)	-0.3	6	V
VI	Input voltage range	Receiver	-25	25	V
	Output voltage reage		-13.2	13.2	V
Vo	Output voltage range	Receiver		V _{CC} + 0.3	V
		DB package		70	
	Package thermal impedance (3)(4)	DW package		58	0000
θ_{JA}		PW package		83	°C/W
	RHL package			TBD	
T_{J}	Operating virtual junction temperature			150	°C
T _{stg}	Storage temperature range			150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

All voltages are with respect to network GND.

Maximum power dissipation is a function of $T_J(max)$, θ_{JA} , and T_A . The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) - T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability. The package thermal impedance is calculated in accordance with JESD 51-7.

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Recommended Operating Conditions⁽¹⁾

See Figure 5

				MIN	NOM	MAX	UNIT
	$V_{CC} = 3.3 \text{ V}$					3.6	\
	Supply voltage	d control high-level input voltage d control low-level input voltage d control input voltage DIN, EN, PWRDOWN DIN, EN, PWRDOWN DIN, EN, PWRDOWN input voltage	$V_{CC} = 5 V$	4.5	5	5.5	V
V	Driver and control high level input voltage	DIN EN DW/DDOWN	V _{CC} = 3.3 V	2			V
V _{IH}	Driver and control high-level input voltage	DIN, EN, PVVKDOVIN	$V_{CC} = 5 V$	2.4			V
V_{IL}	Driver and control low-level input voltage	DIN, EN, PWRDOWN				8.0	V
V_{I}	Driver and control input voltage	DIN, EN, PWRDOWN		0		5.5	V
V_{I}	V _I Receiver input voltage					25	٧
т	Operating free-air temperature		SN75C3222E	0		70	ĵ
T _A	Operating nee-all temperature		SN65C3222E	-40		85	C

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V.

Electrical Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
I	Input leakage current (EN, PWRDOWN)			±0.01	±1	μΑ
	Supply current	No load, PWRDOWN at V _{CC}		0.3	1	mA
ICC	Supply current (powered off)	No load, PWRDOWN at GND		1	10	μΑ

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V. (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

SLLS725A-JUNE 2006-REVISED JULY 2006

DRIVER SECTION

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDI	TIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	DIN = GND	5	5.4		٧
V_{OL}	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND,	$DIN = V_{CC}$	-5	-5.4		٧
I _{IH}	High-level input current	$V_I = V_{CC}$			±0.01	±1	μΑ
$I_{\rm IL}$	Low-level input current	V _I at GND			±0.01	±1	μΑ
I _{OS}	Short-circuit output current ⁽³⁾	$V_{CC} = 3.6 \text{ V}$ $V_{CC} = 5.5 \text{ V}$	V _O = 0 V		±35	±60	mA
r _o	Output resistance	V_{CC} , V+, and V- = 0 V,	V _O = ±2 V	300	10M		Ω
	Output lookogo ourrent	PWRDOWN = GND	$V_{CC} = 3 \text{ V to } 3.6 \text{ V},$ $V_{O} = \pm 12 \text{ V}$			±25	^
I _{OZ}	Output leakage current	FWKDOWIN = GND	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V},$ $V_{O} = \pm 10 \text{ V}$			±25	μΑ

Switching Characteristics⁽¹⁾

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS			MIN	TYP ⁽²⁾	MAX	UNIT	
		_	C _L = 1000 pF		250				
	Maximum data rate (See Figure 1)	$R_L = 3 \text{ k}\Omega$, One DOUT switching	$C_L = 250 \text{ pF},$	V_{CC} = 3 V to 4.5 V	1000			kbit/s	
	(GGC Figure T)	one Boot omicining	$C_L = 1000 \text{ pF},$	$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	1000				
t _{sk(p)}	Pulse skew ⁽³⁾	$C_L = 150 \text{ pF to } 2500 \text{ pF},$	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	See Figure 2		300		ns	
	Slew rate, transition region (see Figure 1)	Slew rate, $R_L = 7 \text{ k}\Omega$,		C _L = 150 pF to 1000 pF		8		90	
SR(tr)		D 010	C _L = 1000 pF		12		60	V/μs	
		Figure 1) $R_L = 3 \text{ k}\Omega$			24		150		

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V. (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and V_{CC} = 5 V. (3) Pulse skew is defined as V_{CC} = 0.1 V_{CC} = 5 V_{CC} = 6 V_{CC} = 6 V_{CC} = 7 V_{CC} = 9 V_{CC} =

Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V. All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

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RECEIVER SECTION

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP ⁽²⁾	MAX	UNIT
V_{OH}	High-level output voltage	$I_{OH} = -1 \text{ mA}$	$V_{CC} - 0.6$	V _{CC} - 0.1		٧
V_{OL}	Low-level output voltage	I _{OL} = 1.6 mA			0.4	٧
V	Desitive gains input threshold valtage	V _{CC} = 3.3 V		1.5	2.4	٧
V _{IT+}	Positive-going input threshold voltage	V _{CC} = 5 V		1.8	2.4	V
V	Negative gains input threehold valtage	V _{CC} = 3.3 V 0.6 1.2			V	
V _{IT}	Negative-going input threshold voltage	V _{CC} = 5 V	0.8	1.5		V
V _{hys}	Input hysteresis (V _{IT+} - V _{IT-})			0.3		V
I _{OZ}	Output leakage current	EN = 1		±0.05	±10	μΑ
r _i	Input resistance	$V_1 = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

⁽¹⁾ Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V. (2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

Switching Characteristics⁽¹⁾

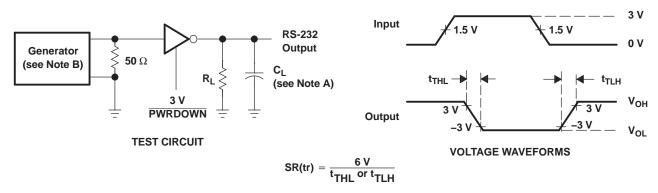
over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	TYP ⁽²⁾	UNIT
t _{PLH}	Propagation delay time, low- to high-level output	C _L = 150 pF, See Figure 3	300	ns
t _{PHL}	Propagation delay time, high- to low-level output	C _L = 150 pF, See Figure 3	300	ns
t _{en}	Output enable time	$C_L = 150 \text{ pF}, R_L = 3 \text{ k}\Omega, \text{ See Figure 4}$	200	ns
t _{dis}	Output disable time	$C_L = 150 \text{ pF}, R_L = 3 \text{ k}\Omega, \text{ See Figure 4}$	200	ns
t _{sk(p)}	Pulse skew ⁽³⁾	See Figure 3	300	ns

Test conditions are C1–C4 = 0.1 μ F at V_{CC} = 3.3 V \pm 0.3 V; C1 = 0.047 μ F, C2–C4 = 0.33 μ F at V_{CC} = 5 V \pm 0.5 V. All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C. Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

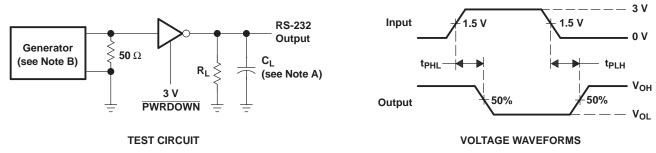
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PARAMETER MEASUREMENT INFORMATION



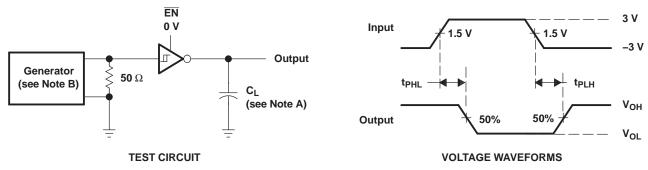
- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 1. Driver Slew Rate



- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s, $Z_O = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 2. Driver Pulse Skew

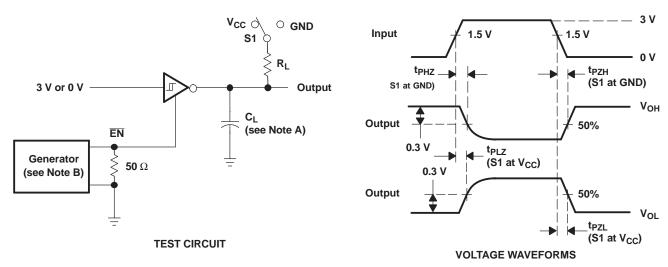


- A. C₁ includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: $Z_0 = 50 \Omega$, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 3. Receiver Propagation Delay Times



PARAMETER MEASUREMENT INFORMATION (continued)

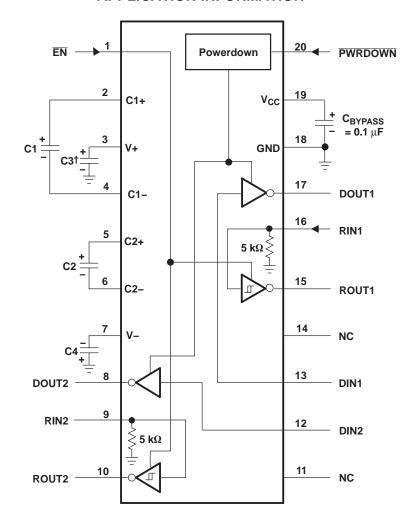


- A. C_L includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: Z_0 = 50 Ω , 50% duty cycle, $t_r \le 10$ ns. $t_f \le 10$ ns.

Figure 4. Receiver Enable and Disable Times

SLLS725A-JUNE 2006-REVISED JULY 2006

APPLICATION INFORMATION



 † C3 can be connected to $V_{CC}\, or \, GND.$

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NOTES: A. Resistor values shown are nominal.

- B. NC No internal connection
 - C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

V _{CC}	C1	C2, C3, and C4
3.3 V \pm 0.3 V	0.1 μ F	0.1 μ F
5 V \pm 0.5 V	0.047 μ F	0.33 μF
3 V to 5.5 V	0.1 μF	0.47 μ F

Figure 5. Typical Operating Circuit and Capacitor Values



PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN65C3222EDB	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EDBG4	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EDBRG4	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EDWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EDWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EDWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EPWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN65C3222EPWRG4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EDB	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EDBG4	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EDBRG4	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EDWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EDWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EDWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EPWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
SN75C3222EPWRG4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:



PACKAGE OPTION ADDENDUM

6-Dec-2006

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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11-Mar-2008

TAPE AND REEL INFORMATION





_		
		Dimension designed to accommodate the component width
Γ	B0	Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
Γ	P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3222EDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN65C3222EDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1
SN65C3222EPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN75C3222EDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN75C3222EDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.0	2.7	12.0	24.0	Q1
SN75C3222EPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
SN65C3222EDBR	SSOP	DB	20	2000	346.0	346.0	33.0	
SN65C3222EDWR	SOIC	DW	20	2000	346.0	346.0	41.0	
SN65C3222EPWR	TSSOP	PW	20	2000	346.0	346.0	33.0	
SN75C3222EDBR	SSOP	DB	20	2000	346.0	346.0	33.0	
SN75C3222EDWR	SOIC	DW	20	2000	346.0	346.0	41.0	
SN75C3222EPWR	TSSOP	PW	20	2000	346.0	346.0	33.0	

DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

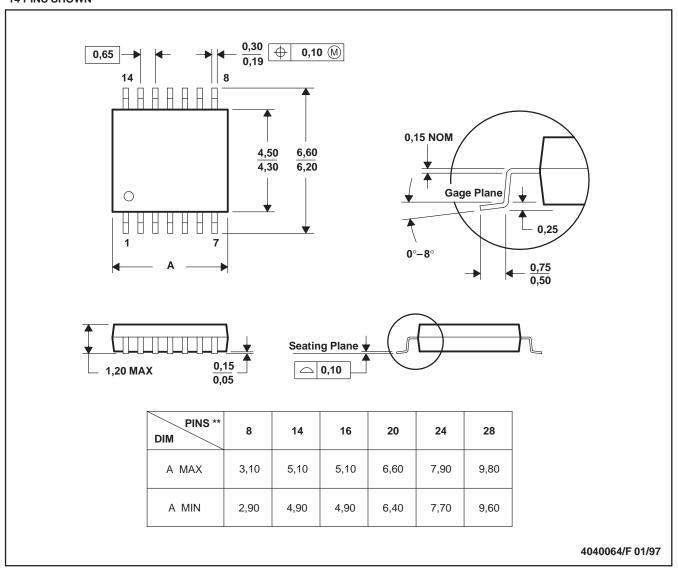
D. Falls within JEDEC MO-150



PW (R-PDSO-G**)

14 PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

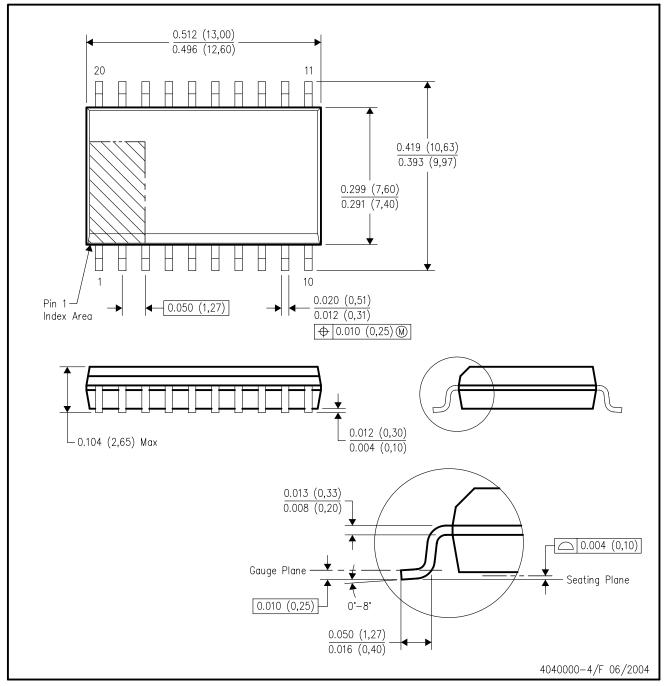
B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

DW (R-PDSO-G20)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



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